Two-dimensional Platinum Diselenide Waveguide-Integrated Infrared Photodetectors

Shayan Parhizkar1,2, Maximilian Prechtl3, Anna Lena Giesecke2,*, Stephan Suckow2, Sophia Wahl4, Sebastian Lukas1, Oliver Hartwig3, Nour Negm1,2, Arne Quellmalz5, Kristinn B. Gylfason5, Daniel Schall2,6, Matthias Wuttig4, Georg S. Duesberg3, and Max C. Lemme1,2,*

1 Chair of Electronic Devices, RWTH Aachen University, Otto-Blumenthal-Str. 2, 52074 Aachen, Germany
2 AMO GmbH, Advanced Microelectronic Center Aachen, Otto-Blumenthal-Str. 25, 52074 Aachen, Germany
3 Institute of Physics, Faculty of Electrical Engineering and Information Technology (EIT 2), Bundeswehr University Munich, Werner-Heisenberg-Weg 39, 85577 Neubiberg, Germany
4 Chair of Experimental Physics (1A), RWTH Aachen University, Sommerfeld-Str 16, 52074 Aachen, Germany
5 Division of Micro and Nanosystems, School of Electrical Engineering and Computer Science, KTH Royal Institute of Technology, SE-10044 Stockholm, Sweden
6 Black Semiconductor GmbH, Monnetweg 23, 52066, Aachen Germany

KEYWORDS: platinum diselenide, photodetector, silicon photonics, 2-dimensional materials, infrared
Abstract

Low cost, easily integrable photodetectors (PDs) for silicon (Si) photonics are still a bottleneck for photonic integrated circuits (PICs), especially for wavelengths above 1.8 µm. Multilayered platinum diselenide (PtSe$_2$) is a semi-metallic two-dimensional (2D) material that can be synthesized below 450°C. We integrate PtSe$_2$ based PDs directly by conformal growth on Si waveguides. The PDs operate at 1550 nm wavelength with a maximum responsivity of 11 mA/W and response times below 8.4 µs. Fourier transform infrared spectroscopy (FTIR) in the wavelength range from 1.25 µm to 28 µm indicates the suitability of PtSe$_2$ for PDs far into the infrared wavelength range. Our PtSe$_2$ PDs integrated by direct growth outperform PtSe$_2$ PDs manufactured by standard 2D layer transfer. The combination of IR responsivity, chemical stability, selective and conformal growth at low temperatures, and the potential for high carrier mobility, make PtSe$_2$ an attractive 2D material for optoelectronics and PICs.
Introduction

Photonic integrated circuits (PICs) are maturing as a platform for applications in telecommunications, spectroscopy, diagnostics, biomedical imaging, and gas sensing. PICs tailored for these applications typically rely on infrared (IR) photodetectors that are coupled to waveguides and that function as essential components for optoelectronic signal conversion. Photodetectors for the near-infrared wavelength range are mainly based on widely used semiconductors such as Si² and Ge³. Mid-infrared photodetectors are typically made from compound semiconductors such as InGaAs⁴ and HgCdTe⁵, with the downside of higher manufacturing cost and the necessity of cryogenic temperature operating conditions. However, a key requirement towards broad applicability of PICs is the integrability of IR photodetectors on photonic waveguides. This is not fulfilled by commercial manufacturing methods for the conventional materials, because their high deposition and (epitaxial) growth temperatures are not compatible with PIC thermal budgets. This creates a demand for infrared photodetectors with high manufacturability at low temperature budgets.

Two-dimensional (2D) materials have attracted tremendous attention in the optoelectronics field due to their broadband optical absorption, high carrier mobility, mechanical flexibility and ease of integration.⁶⁻⁹ In particular, the zero-bandgap material graphene has been used to demonstrate high performance integrated photodetectors and modulators in the IR.¹⁰⁻¹⁴ However, graphene requires a layer transfer process,¹⁵,¹⁶ because its growth is limited to a few substrate materials and requires high temperatures. 2D black phosphorus is also suitable as an IR PD¹⁷,¹⁸ material that can be transferred onto waveguides,¹⁹,²⁰ but has the drawback that it is not entirely stable in ambient conditions.²¹ Platinum diselenide (PtSe₂) is a transition metal dichalcogenide (TMD) with an octahedral lattice structure that is semiconducting with an indirect bandgap of 1.2 eV as
a monolayer. As a multilayer material, it becomes semi-metallic.\textsuperscript{22} This semi-metallic nature of layered PtSe\textsubscript{2} allows its use for broadband IR-photodetection in a similar way to graphene.\textsuperscript{23-25} In addition, PtSe\textsubscript{2} is stable in air and has a high charge carrier mobility compared to other TMDs, with theoretically predicted values of more than 1,000 cm\textsuperscript{2}/Vs.\textsuperscript{26,27} A major advantage of PtSe\textsubscript{2} is the possibility of direct, large-scale growth on various substrates at temperatures below 450°C using the thermally assisted conversion (TAC) technique.\textsuperscript{23,28-30} In combination with the potential for selective and conformal deposition,\textsuperscript{31} PtSe\textsubscript{2} is suitable for back-end-of-line (BEOL) integration on electronic and photonic wafers.

In this work, we demonstrate the use of layered PtSe\textsubscript{2} as integrated IR photodetectors on Si photonic waveguides. We compare the device performance and material quality of a direct-growth integration approach with a wet layer transfer technique through analytical, electrical, and optical characterization.

**Experimental:**

The PtSe\textsubscript{2} photodetectors were realized on rib-waveguides with 50 nm step height on silicon on insulator (SOI) substrates. Optical access is provided through two grating couplers that are optimized for a wavelength of 1550 nm and transverse electric (TE) polarization. We fabricated two sets of samples, one using a direct-growth and a second one using a wet-transfer method of the PtSe\textsubscript{2} layers. For the first set, a 10.8 nm thick layer of pre-patterned sputtered platinum (Pt) was converted into a 27 nm thick layered film of PtSe\textsubscript{2} directly on the waveguides using TAC.\textsuperscript{23} For the second set of samples, PtSe\textsubscript{2} films of 7.6, 13.7, and 23.5 nm thickness were grown by TAC on separate silicon substrates with a 90 nm thermal silicon oxide (SiO\textsubscript{2}) layer and were wet transferred onto the Si waveguides (see Methods for details). The thicknesses of the PtSe\textsubscript{2} films
were measured by atomic force microscopy (AFM) (supporting information). In both sample sets, the PtSe$_2$ patches were contacted with nickel/aluminum electrodes that had a distance of 5 $\mu$m to the waveguides. The width of the PtSe$_2$ channels on the waveguide along the light propagation direction for all photodetectors is $W = 50$ $\mu$m. Schematic cross sections of the integrated photodetectors and scanning electron microscope (SEM) images of a transferred and a directly grown photodetector are shown in Fig. 1 a-d.
Figure 1. Schematic cross sections and false color scanning electron microscope (SEM) micrographs of transferred (a, c) and directly grown (b, d) PtSe$_2$ photodetectors on silicon waveguides. The wrinkles visible in the SEM image in c) are due to wet transfer, and consequently absent in d). The green dashed lines indicate the direction of the cross sections in a) and b).

The topography of the PtSe$_2$ films around the waveguides is different for the two different integration methods. The wet transfer method presumably leads to small air gaps around the sidewalls of the Si waveguides, which is known from graphene devices, as indicated schematically in Fig. 1a. With the wet transfer process, the conformal coverage around the waveguide is not possible because of the limited flexibility of the transfer polymer. In addition, wrinkles in the PtSe$_2$ layer are visible that result from the wet transfer process (Fig. 1c). In the case of directly grown PtSe$_2$, the sputtered Pt covers the sidewalls of the waveguides which results in a conformal PtSe$_2$ film around the waveguide (Fig. 1b and d). This feature underlines
the advantage of direct 2D material growth over layer transfer which often requires additional planarization processes to avoid tearing of the 2D films at the sharp edges of the waveguides.\textsuperscript{13,33}

Raman spectroscopy was carried out on all devices to confirm the successful formation and quality of PtSe\textsubscript{2} layers after fabrication (Fig. 2a). The spectra of various PtSe\textsubscript{2} films on silicon-on-insulator substrate exhibit two characteristic peaks at approximately 177 cm\textsuperscript{-1} and 206 cm\textsuperscript{-1}, which represent the E\textsubscript{g} and A\textsubscript{1g} modes of layered PtSe\textsubscript{2}, respectively.\textsuperscript{34} The E\textsubscript{g} peak originates from the in-plane vibration of selenium (Se) atoms and the A\textsubscript{1g} peak is caused by out of plane vibration of Se atoms. As the number of PtSe\textsubscript{2} layers increases, a red shift in the position of both peaks and an increase in the intensity ratio of the two peaks I(A\textsubscript{1g})/I(E\textsubscript{g}) is observed. This behavior can be explained by an increasing out-of-plane contribution due to an increase of Vander-Waals interactions between the layers.\textsuperscript{34} The full width at half maximum (FWHM) of the E\textsubscript{g} peak indicates the material quality of PtSe\textsubscript{2}.\textsuperscript{35,36} For high quality TAC-grown PtSe\textsubscript{2} films, the FWHM is smaller than 5 cm\textsuperscript{-1}.\textsuperscript{37} For our samples with a directly grown PtSe\textsubscript{2} film the FWHM of the E\textsubscript{g} peak is 4.8 cm\textsuperscript{-1}. For the samples with transferred PtSe\textsubscript{2}, this value varies between 5.1 and 5.6 cm\textsuperscript{-1}. In both cases, these values indicate high material quality which is sufficient for device integration.\textsuperscript{37}
Figure 2. a) Raman spectra of PtSe$_2$ with different thicknesses of transferred PtSe$_2$ (gray, red, and blue lines) and direct growth (green line). The spectra represent the average of area scans. They were recorded with an integration time of 1 s and averaged over 10 accumulations. b) Drain current ($I_{ds}$) as a function of drain-source voltage ($V_{ds}$) for different PtSe$_2$ photodetectors. c) Evanescent field absorption of PtSe$_2$ films on the waveguide at 1550 nm wavelength. The absorption per propagation distance for 7.6 nm, 13.7 nm, 23.5 nm, and 27 nm thick (directly grown) PtSe$_2$ is 0.06, 0.38, 0.85, and 1.2 dB/μm.

Current-voltage (IV) measurements of the PtSe$_2$ detectors with different thicknesses show linear behavior throughout, which indicates the semi-metallic nature of the PtSe$_2$ films and ohmic contacts to the Ni/Al electrodes. The resistance of PtSe$_2$ decreases with increasing layer
thickness. The directly grown PtSe$_2$ layer exhibits similar semi-metallic properties as the transferred layers. This is an important observation because the direct growth process includes Pt deposition and TAC on the sidewalls and at the edges and corners. This finding thus demonstrates the potential of direct integration of PtSe$_2$ on photonic structures. The resistivities of nickel/aluminum contacts to PtSe$_2$ films have been measured with the transfer length method (TLM) to vary between 0.7 and 2 kΩ µm for the same batch of samples in a previous study. Such values allow us to neglect the effect of the metal contacts on the total device resistance and use the two-probe configuration for further analysis.

The light-matter interaction of the PtSe$_2$ films was characterized for infrared light with a wavelength of $\lambda = 1550$ nm that was coupled into one grating coupler through a single-mode fiber. The fiber-to-fiber losses of the grating couplers and the waveguides of 8 dB were measured on separate test structures and subtracted to obtain these values. First, we measured the specific absorption of the evanescent field by the PtSe$_2$ films located at 10 nm distance to the waveguide, using structures with different PtSe$_2$ dimensions (Fig. 2c). The resulting absorption was 0.06, 0.38, 0.85, and 1.2 dB/µm for 7.6, 13.7, 23.5 and 27 nm PtSe$_2$, respectively.

The opto-electric response of the PtSe$_2$ photodetectors was investigated by measuring the photocurrents with a lock-in amplifier, while modulating the light intensity at a frequency of 1 kHz (see also supporting information). The photocurrents were measured as a function of laser light power for each photodetector with a width of 50 µm (along the waveguides) and a length of 13 µm (perpendicular to the waveguides, i.e. distance between the contacts) for an applied bias voltage of $V_{ds} = 4.5$ V across the device. All detectors exhibit a linear dependence on light power for the measured range. The highest photocurrent is observed for the device with a directly
grown PtSe₂ film (Fig. 3a). Measurements of the photocurrents at different bias voltages ranging from \( V_{ds} = -4.5 \) V to 4.5 V at a fixed laser output power of 9 mW are plotted in Fig. 3b. Increasing \( V_{ds} \) results in higher photocurrents. The intrinsic responsivity is defined as \( R = \frac{I_{ph}}{P_{opt}} \), where \( I_{ph} \) is the photocurrent and \( P_{opt} \) is the optical power arriving at the photodetector after subtracting the losses of the grating couplers and waveguides. At 4.5 V applied bias voltage, this intrinsic responsivity yields \( R = 0.8 \) mA/W for the thinnest PtSe₂ layer (7.6 nm) up to a maximum value of \( R = 11 \) mA/W for the photodetector with a directly grown PtSe₂ layer of 27 nm thickness (Table 1). Different devices on each chip were measured and statistics of the responsivities are also shown in Fig. 3c, which confirms that the responsivity of the devices increases with the number of PtSe₂ layers.
Figure 3. Optical measurements of PtSe$_2$ photodetectors. All devices are 50 $\mu$m wide along the waveguide direction. a) Photocurrent as a function of light power at 4.5 V bias voltage. All PtSe$_2$ photodetectors respond linearly to the light power. b) Photocurrent versus bias voltage at 9 mW laser output power. c) Box plot of responsivities for different thickness PtSe$_2$ photodetectors measured at 4.5 V applied bias. d) Time resolved measurement of the PtSe$_2$ photodetectors. The measured rise and fall times for the devices are between 8 and 13 $\mu$s.

The normalized photocurrent to dark current ratio (NPDR), defined as responsivity divided by the dark current, is another important parameter for evaluating the sensitivity of the photodetectors. Larger NPDR values indicate better suppression of dark currents and lower noise-equivalent power. NPDRs of all the photodetectors have been calculated and listed in
Table 1. The NPDR values for the PtSe₂ photodetectors are similar to those reported for graphene photodetectors, but have the strong advantage of enabling direct growth instead of transfer.^1^1,^3^8

Time-resolved measurements were performed on the PtSe₂ photodetectors (Fig. 3d). The rise and fall time are defined by the time it takes for the photocurrent to reach 10 % and 90 % of the maximum value in rising and decaying curves, respectively, or by fitting equations 1 and 2:^3^9

\[ I_{\text{rise}} = I_0 + Ae^{\left(\frac{t-t_1}{\tau}\right)} \]  
(eq. 1)

\[ I_{\text{fall}} = I_0 + Be^{-\left(\frac{t-t_2}{\tau}\right)} \]  
(eq. 2)

where \( \tau \) is the rise/fall time constant and \( t_1 \) or \( t_2 \) is the time, it takes for switching the laser on or off, respectively. The measured rise and fall times for the photodetectors are listed in table 1. The values for all the detectors are between 8 and 13 \( \mu s \). Consequently, our photodetectors provide a faster response time than most of the reported TMD-based IR photodetectors so far.^4^0,^4^1 The performance parameters of merit for some 2D-based infrared photodetectors are summarized in Table 2. The transient time (\( \tau_t \)), i.e. the time needed for the photocarriers to reach the metal contacts, can be calculated through the carrier drift model by equation 3:^4^2

\[ \tau_t = \frac{L^2}{2\mu V_{ds}} \]  
(eq. 3)

where \( L \) is the length of the channel perpendicular to the propagation of the light, \( \mu \) is the electron mobility and \( V_{ds} \) is the applied bias. To approximate the carrier mobility, PtSe₂ films with the same thicknesses as used for the photodetectors and grown in the same batch were wet transferred onto a Si substrate with 90 nm SiO₂ layer. After fabrication of the contacts and
patterning of the PSe$_2$ films, the field effect mobility of all the film thicknesses were calculated using the transconductance method in equation 4.$^{43,44}$

$$\mu = g_m \frac{L}{W V_{ds} C_g} \quad \text{(eq. 4)}$$

Here, W is the channel width along the waveguide and $V_{ds}$ is the voltage applied to the device channel. $g_m$ is defined as $\frac{dI_{ds}}{dV_g}$ where $I_{ds}$ is the drain-source current and $V_g$ is the back gate voltage, and $C_g = \frac{\epsilon \epsilon_0}{t_{ox}}$ is the back gate capacitance of SiO$_2$. $\epsilon$ and $\epsilon_0$ are the relative and vacuum permittivity and $t_{ox}$ is the thickness of SiO$_2$. The extracted field effect mobilities for all PtSe$_2$ films were between 2.7 to 3.9 cm$^2$/Vs. This relatively low value can be attributed to defects and the polycrystallinity of the films.$^{27,45}$ Using the extracted carrier mobility, the transient time for a device with $L = 13 \mu m$ and 4.5 V bias voltage is 0.6 ns.
Table 1. Summary of the different PtSe$_2$ photodetectors. Maximum responsivity, normalized photocurrent to dark current ratio (NPDR) and rise/fall time of all the photodetectors.

<table>
<thead>
<tr>
<th>PtSe$_2$</th>
<th>Thickness (nm)$^a$</th>
<th>Number of layers (estimate)</th>
<th>Absorption (dB/$\mu$m)</th>
<th>Max responsivity (mA/W)$^b$</th>
<th>NPDR (W$^{-1}$)$^b$</th>
<th>Rise/fall time ($\mu$s)$^b$</th>
</tr>
</thead>
<tbody>
<tr>
<td>Sample A: Grown on Si/SiO$_2$, wet transferred</td>
<td>7.6</td>
<td>11</td>
<td>0.6</td>
<td>0.87</td>
<td>7.5</td>
<td>8.6/13.1</td>
</tr>
<tr>
<td>Sample B: Grown on Si/SiO$_2$, wet transferred</td>
<td>13.7</td>
<td>20</td>
<td>0.38</td>
<td>2.2</td>
<td>1.3</td>
<td>8.7/9.9</td>
</tr>
<tr>
<td>Sample C: Grown on Si/SiO$_2$, wet transferred</td>
<td>23.5</td>
<td>34</td>
<td>0.85</td>
<td>7.5</td>
<td>1.6</td>
<td>8.5/9.7</td>
</tr>
<tr>
<td>Sample D: Directly grown on Si waveguide</td>
<td>27</td>
<td>39</td>
<td>1.2</td>
<td>11</td>
<td>1.9</td>
<td>8.4/8.7</td>
</tr>
</tbody>
</table>

(a) A single layer PtSe$_2$ has a thickness of about 0.7 nm.$^{46}$ Number of layers for each film can be estimated accordingly.

(b) Reported at 4.5 V bias voltage

Potential applications for photonics-integrated IR photodetectors beyond the telecommunication wavelengths are sensing, diagnostics, thermal imaging, and free space communication.$^{44,47}$ Therefore, we have studied the broad-band absorption of PtSe$_2$ films with different thicknesses for the wavelength range from 1.2 to 28 $\mu$m using Fourier transform infrared spectroscopy (FTIR). We wet transferred PtSe$_2$ films with thicknesses of 7.6, 13.7, and 23.5 nm onto separate Si substrates and measured their absorbance (A) by FTIR spectroscopy, while subtracting the absorbance of the Si substrate (Fig. 4a). All PtSe$_2$ films exhibit a small peak at 1729 cm$^{-1}$ (5784 nm). The absorption coefficients ($\alpha$) of the PtSe$_2$ films were also calculated from their absorbance by equation 5,
\[ A \ln(10) = \alpha t \]  \hspace{1cm} (eq. 5)

where \( A \) is the absorbance of the material and \( t \) is the film’s thickness (Fig. 4b). The absorption coefficient of the sample with the thickest PtSe\(_2\) (23.5 nm) layer behaves differently from the other two samples: while its absorption decreases at first in a similar way as the 7.6 and 13.7 nm thick films, it starts to increase to a steady value as the wavelength increases further. The coefficients of the thinner films remain low as the wavelength increases. The absorption of the 23.5 nm thick PtSe\(_2\) is non-zero even at 28 \( \mu \)m wavelength (0.04 eV) which can be considered metallic behavior.\(^{48}\) This result suggests that PtSe\(_2\) may also be suitable for long wavelength mid-IR photodetectors.

Figure 4. a) Absorbance of PtSe\(_2\) by the use FTIR spectroscopy. Inset: Magnified view of the peak at 1729 cm\(^{-1}\) (5784 nm). b) Absorption coefficients of PtSe\(_2\) films with different thicknesses, calculated from their absorbance.

We have demonstrated the integration of PtSe\(_2\) photodetectors into silicon photonics waveguides and demonstrated their functionality at a wavelength of 1550 nm. We have shown that layered PtSe\(_2\) can be utilized for infrared photodetection with high responsivity. Our PtSe\(_2\) photodetectors can be synthesized directly on the photonic waveguide structures, on wafer scale
and at CMOS compatible temperatures using TAC. The directly grown films show higher performance than reference devices transferred with a typical 2D layer transfer method. The highest responsivity of 11 mA/W was achieved for a directly grown PtSe₂ photodetector, which reached a fast response time of 8.4 μs. FTIR data indicate that PtSe₂ is suitable for photodetection well into the mid-IR range, which opens opportunities for applications in food safety, agriculture, gas detection, on-chip spectroscopy, or imaging. The direct growth of PtSe₂ on waveguides creates a new perspective for the integration of 2D materials with photonic integrated circuits. Our results show that multi-layered PtSe₂ is a promising candidate for high-responsivity optoelectronic applications in the near and mid IR regime, including the direct integration on commercial semiconductor technology platforms. This includes silicon nitride (SiN) photonics, as the growth methods does not require any crystalline surfaces, in contrast to epitaxial processes.⁹⁹⁻⁶⁻¹

Table 2. Characteristics and performance metrics of photodetectors based on 2D materials.

<table>
<thead>
<tr>
<th>Materials</th>
<th>Growth methods</th>
<th>Wavelength</th>
<th>Responsivity</th>
<th>Response time</th>
<th>Ref.</th>
</tr>
</thead>
<tbody>
<tr>
<td>Graphene</td>
<td>CVD</td>
<td>1550 nm</td>
<td>180 mA/W</td>
<td>2.7 ps*</td>
<td>⁵²</td>
</tr>
<tr>
<td>BP</td>
<td>Exfoliation</td>
<td>3.8 μm</td>
<td>11.3 A/W</td>
<td>0.3 ms</td>
<td>⁵³</td>
</tr>
<tr>
<td>MoS₂</td>
<td>MOVPE</td>
<td>360 - 960 nm</td>
<td>920 A/W</td>
<td>0.5/1.15 s</td>
<td>⁴¹</td>
</tr>
<tr>
<td>MoS₂</td>
<td>Exfoliation</td>
<td>980 nm</td>
<td>2.3 A/W</td>
<td>50 ms</td>
<td>⁵⁴</td>
</tr>
<tr>
<td>HfS₂</td>
<td>CVD</td>
<td>808</td>
<td>3.8 x 10⁵ A/W</td>
<td>8 ms</td>
<td>⁵⁵</td>
</tr>
<tr>
<td>MoTe₂</td>
<td>CVD</td>
<td>980</td>
<td>6.4 A/W</td>
<td>31/21 ms</td>
<td>⁵⁶</td>
</tr>
<tr>
<td>PtSe₂</td>
<td>TAC</td>
<td>635 nm – 2.7 μm</td>
<td>7.8 mA/W</td>
<td>6/9 µs</td>
<td>²⁵</td>
</tr>
<tr>
<td>PtSe₂</td>
<td>CVD</td>
<td>1550 nm</td>
<td>0.19 mA/W</td>
<td>17/39 ps</td>
<td>⁵⁷</td>
</tr>
<tr>
<td>PtSe₂</td>
<td>TAC</td>
<td>1550 nm</td>
<td>11 mA/W</td>
<td>8.4/8.7 μs</td>
<td>This work</td>
</tr>
</tbody>
</table>

* Calculated from reported 3 dB bandwidth.
Methods

Device Fabrication: silicon rib waveguides with 50 nm step height were fabricated on a 150 mm SOI wafer with 220 nm top Si and 3 µm buried oxide layers using i-line (365 nm) photolithography and reactive ion etching (RIE). Grating couplers designed for 1550 nm wavelength were realized at the end of the waveguides by electron beam lithography and subsequent RIE. 10 nm Al₂O₃ were deposited on the wafer by atomic layer deposition to protect the waveguides and grating couplers from unwanted damage during further process steps and to avoid Schottky junction formation between PtSe₂ and the bottom Si. The thin Al₂O₃ works as a cladding for grating couplers and increases their coupling efficiency.

The SOI wafer was diced after fabricating the photonic base components and PtSe₂ photodetectors were fabricated on different dies of the wafer.

For the directly grown sample, a 10.8 nm Pt layer was sputtered onto the waveguides using a pre-defined lithography pattern and a lift-off process. The Pt layer was converted into PtSe₂ of 27 nm thickness. PtSe₂ films with thicknesses of 7.6, 13.7, and 23.5 nm were grown on separate Si/SiO₂ (90 nm) substrates and then wet transferred onto the separate samples using potassium hydroxide (KOH) solution. All PtSe₂ films were grown using this TAC process, described in detail in previous publications.²³-³⁴ For wet transfer a support layer of Poly (methyl methacrylate) (PMMA) was spincoated on top of the PtSe₂ films. Then PMMA film was scratched, and few droplets of KOH solution were dropped on the scratched areas. KOH causes delamination of PtSe₂ films from underlying SiO₂. After delamination and release of PtSe₂/PMMA films from the substrates, they remained floating on the deionized water for few days and then were transferred on the final substrates using fishing technique. The samples were dried in air and then PMMA layer was removed from their surfaces using acetone and isopropanol. Transferred PtSe₂ films
were patterned using contact lithography and reactive ion etching. Afterwards, all PtSe$_2$ films were contacted with 15 nm Ni and 50 nm Al using contact lithography and subsequently lift off process.

   Electrical characterization: Electrical measurements were performed in a Lakeshore chamber connected to a Keithley SCS4200 source meter unit at ambient conditions.

   FTIR measurements: The absorption spectra were calculated from transmittance measurements. The data was recorded from 0.05 eV (400 cm$^{-1}$) up to 0.99 eV (8000 cm$^{-1}$) in a Bruker Vertex 80v Fourier-transform spectrometer with a spectral resolution of 0.5 meV (4 cm$^{-1}$) and averaged over 64 scans.

AUTHOR INFORMATION

Corresponding Author

* giesecke@amo.de, max.lemme@eld.rwth-aachen.de

ACKNOWLEDGMENT

This work has received funding from the European Union's Horizon 2020 research and innovation programme under grant agreements 825272 (ULISSES) and 881603 (Graphene Flagship), as well as the German Ministry of Education and Research (BMBF) under grant agreement 16ES1121 (NobleNEMS).
REFERENCES


